SILICON EPITAXIAL SCHOTTKY BARRIER DIODE

Features

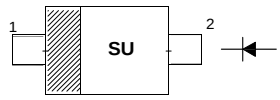
- Low forward voltage
- Low reverse current

Applications

- High Speed Switching

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



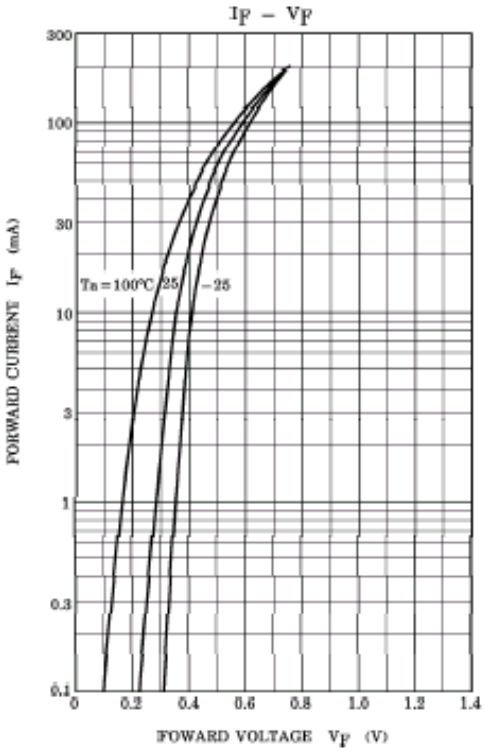
Top View
Marking Code: "**SU**"
Simplified outline SOD-323 and symbol

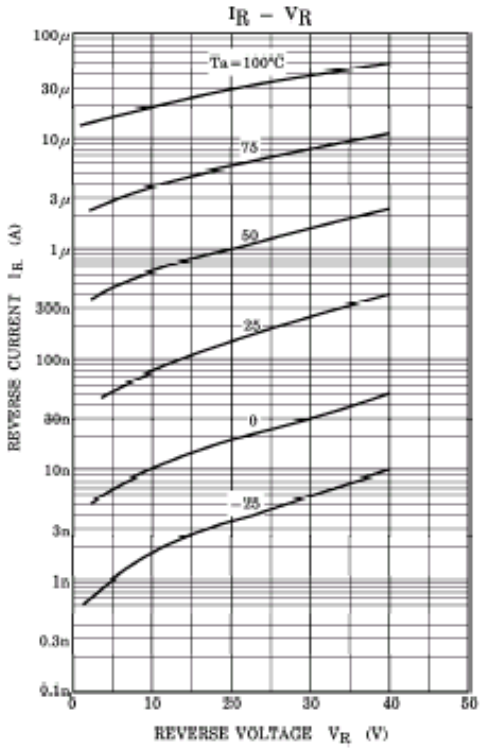
Absolute Maximum Ratings (T_a = 25 °C)

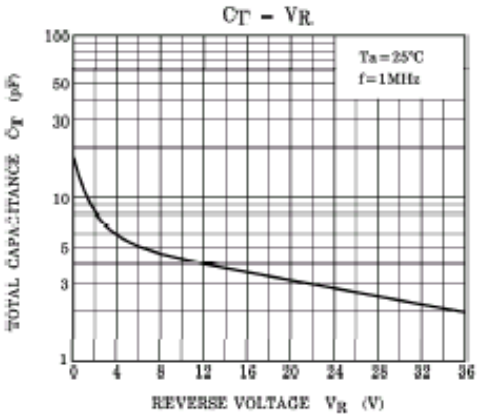
Parameter	Symbol	Value	Unit
Maximum (Peak) Reverse Voltage	V_{RM}	45	V
Reverse Voltage	V_R	40	V
Average Forward Current	I_O	100	mA
Maximum (Peak) Forward Current	I_{FM}	300	mA
Surge Forward Current (10 ms)	I_{FSM}	1	A
Power Dissipation	P_{tot}	150	mW
Junction Temperature	T_J	125	°C
Operating Temperature Range	T_{opr}	- 40 to + 100	°C
Storage Temperature Range	T_{stg}	- 55 to + 125	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Max.	Unit
Forward Voltage at I_F = 100 mA	V_F	0.6	V
Reverse Current at V_R = 40 V	I_R	5	µA
Total Capacitance at f = 1 MHz	C_T	25	pF

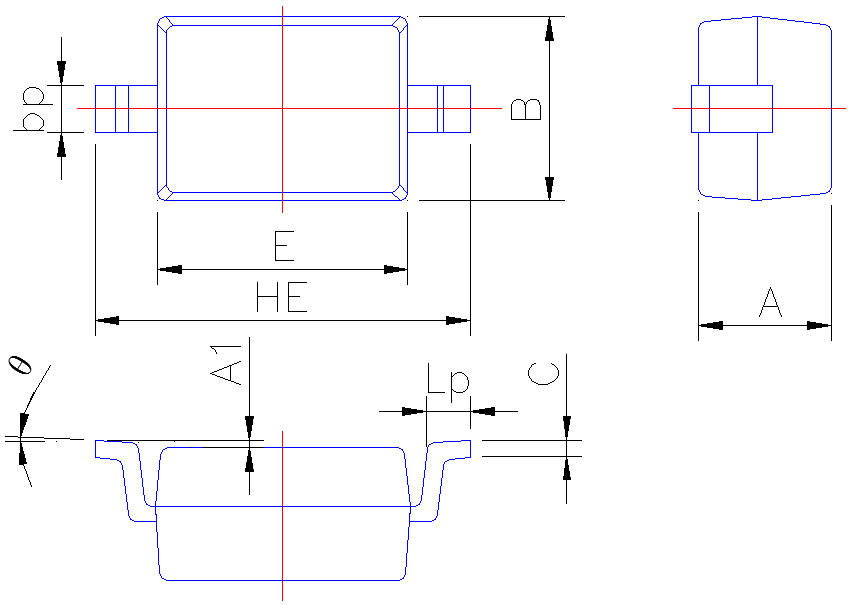






PACKAGE OUTLINE

Plastic surface mounted package; 2 leads **SOD-323**



Symbol	Dimension in Millimeters	
	Min	Max
A	0.95	1.15
A1	0.010	0.100
B	1.20	1.40
bp	0.25	0.40
C	0.09	0.150
E	1.60	1.80
HE	2.30	2.70
Lp	0.20	0.40
θ	0°	5°